

isc Triacs

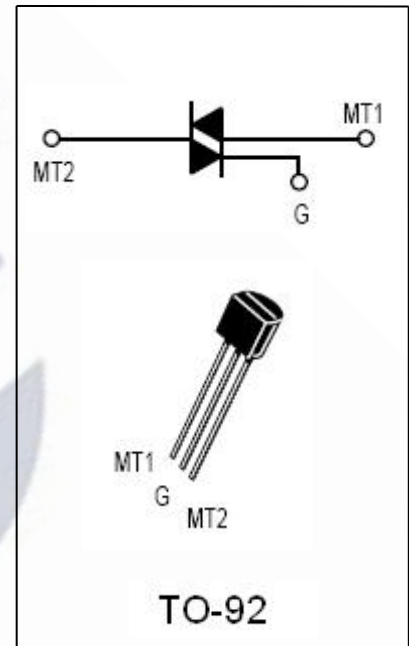
BT131-800

FEATURES

- With TO-92 package
- Glass passivated, sensitive gate triacs in a plastic envelope
- Intended for use in general purpose bidirectional switching and phase control applications.
- These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuit.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	800	V
V_{RRM}	Repetitive peak off-state voltage	800	V
$I_{\text{T(RMS)}}$	RMS on-state current (full sine wave) $T_{\text{lead}} \leq 51^{\circ}\text{C}$	1	A
I_{TSM}	Non-repetitive peak on-state current	10	A
P_{GM}	Peak gate power dissipation	5	W
$P_{\text{G(AV)}}$	Average gate power dissipation	0.5	W
T_j	Operating junction temperature	110	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-40~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{DRM}	Repetitive peak off-state voltage	$I_D=0.1\text{mA}$	800		V
V_{RRM}	Repetitive peak reverse voltage	$I_D=0.5\text{mA}$	800		V
I_D	Off-state leakage current	$V_D = V_{\text{DRM(max)}}$, $T_j = 125^{\circ}\text{C}$		0.5	mA
I_{GT}	Gate trigger current	$V_D=12\text{V}$; $I_T=0.1\text{A}$		3	mA
				3	
				3	
				7	
V_{TM}	On-state voltage	$I_T=2.0\text{A}$		1.7	V
I_H	Holding current	$I_{\text{GT}}=0.1\text{A}$, $V_D=12\text{V}$		5	mA
V_{GT}	Gate trigger voltage	$V_D=12\text{V}$; $R_L=100\ \Omega$ all quadrant		1.5	V